

Features

- P-Channel, -5V Logic Level Control
- Very low on-resistance RDS(on) @ $V_{GS}=-4.5$ V
- Fast Switching
- Enhancement mode
- Pb-free lead plating; RoHS compliant

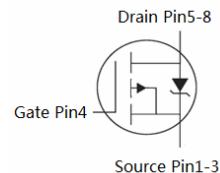
V_{DS}	-30	V
$R_{DS(on),TYP} @ V_{GS}=-10$ V	5.0	mΩ
$R_{DS(on),TYP} @ V_{GS}=-4.5$ V	7.0	mΩ
I_D	-18	A

SOP8



Halogen-Free

Part ID	Package Type	Marking	Tape and reel information
VSO004P03MS	SOP8	004P03M	3000pcs/Reel



Maximum ratings, at $T_j=25$ °C, unless otherwise specified

Symbol	Parameter	Rating	Unit	
Common Ratings (Tc=25°C Unless Otherwise Noted)				
V_{GS}	Gate-Source Voltage	±20	V	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	-30	V	
T_J	Maximum Junction Temperature	150	°C	
T_{STG}	Storage Temperature Range①	-55 to 175	°C	
I_S	Diode Continuous Forward Current	$T_c=25$ °C	-18	A
Mounted on Large Heat Sink				
I_D	Continuous Drain current @ $V_{GS}=-10$ V	$T_c=25$ °C	-18	A
		$T_c=100$ °C	-11.5	A
I_{DM}	Pulse Drain Current Tested ②	$T_c=25$ °C	-72	A
P_D	Maximum Power Dissipation	$T_c=25$ °C	2	W
R_{JJC}	Thermal Resistance-Junction to Case		24	°C/W
R_{JA}	Thermal Resistance Junction-Ambient		62.5	°C/W

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_D=-250\mu\text{A}$	-30	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current($T_c=25^\circ\text{C}$)	$V_{\text{DS}}=-24\text{V}$, $V_{\text{GS}}=0\text{V}$	--	--	-1	μA
	Zero Gate Voltage Drain Current($T_c=125^\circ\text{C}$)	$V_{\text{DS}}=-24\text{V}$, $V_{\text{GS}}=0\text{V}$	--	--	-100	μA
I_{GSS}	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$	--	--	± 100	nA
$V_{\text{GS}(\text{TH})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$, $I_D=-250\mu\text{A}$	-1.0	-1.6	-2.5	V
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance ②	$V_{\text{GS}}=-10\text{V}$, $I_D=-10\text{A}$	--	5.0	6.0	$\text{m}\Omega$
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance ②	$V_{\text{GS}}=-4.5\text{V}$, $I_D=-5\text{A}$	--	7.0	8.0	$\text{m}\Omega$
Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)						
C_{iss}	Input Capacitance	$V_{\text{DS}}=-15\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	--	5960	--	pF
C_{oss}	Output Capacitance		--	585	--	pF
C_{rss}	Reverse Transfer Capacitance		--	415	--	pF
Q_g	Total Gate Charge	$V_{\text{DS}}=-15\text{V}$, $I_D=-10\text{A}$, $V_{\text{GS}}=-10\text{V}$	--	85	--	nC
Q_{gs}	Gate-Source Charge		--	18	--	nC
Q_{gd}	Gate-Drain Charge		--	28	--	nC
Switching Characteristics						
$t_{\text{d(on)}}$	Turn-on Delay Time	$V_{\text{DD}}=-15\text{V}$, $I_D=-5\text{A}$, $R_G=6.8\Omega$, $V_{\text{GS}}=-10\text{V}$	--	18	--	nS
t_r	Turn-on Rise Time		--	22	--	nS
$t_{\text{d(off)}}$	Turn-Off Delay Time		--	86	--	nS
t_f	Turn-Off Fall Time		--	45	--	nS
Source- Drain Diode Characteristics@ $T_J = 25^\circ\text{C}$ (unless otherwise stated)						
V_{SD}	Forward on voltage	$I_{\text{sd}}=-10\text{A}$, $V_{\text{GS}}=0\text{V}$	--	-0.78	-1.3	V
t_{rr}	Reverse Recovery Time	$T_J=25^\circ\text{C}$, $I_{\text{sd}}=-10\text{A}$, $V_{\text{GS}}=0\text{V}$ $dI/dt=-100\text{A}/\mu\text{s}$	--	42	--	nS
Q_{rr}	Reverse Recovery Charge			33		nC

NOTE:

① Repetitive rating; pulse width limited by max. junction temperature.

②Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

Typical Characteristics

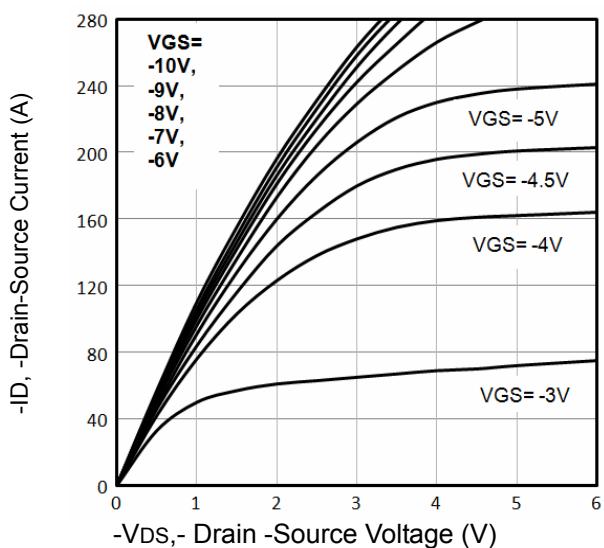


Fig1. Typical Output Characteristics

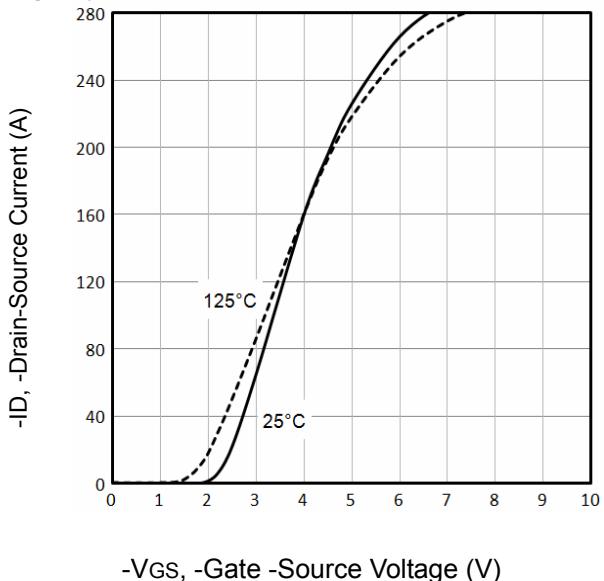


Fig3. Typical Transfer Characteristics

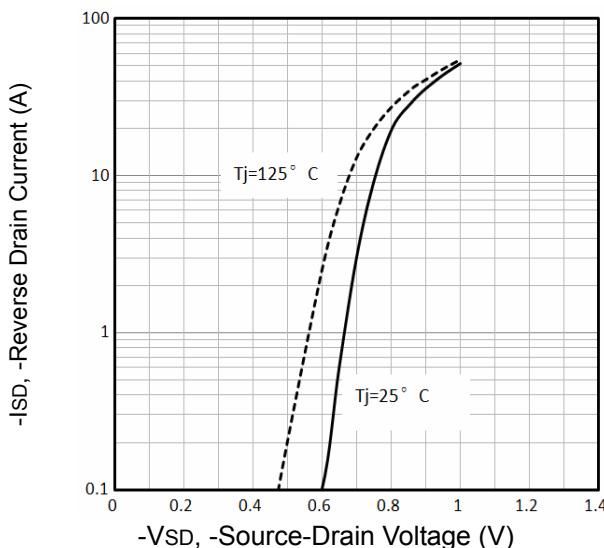


Fig5. Typical Source-Drain Diode Forward Voltage

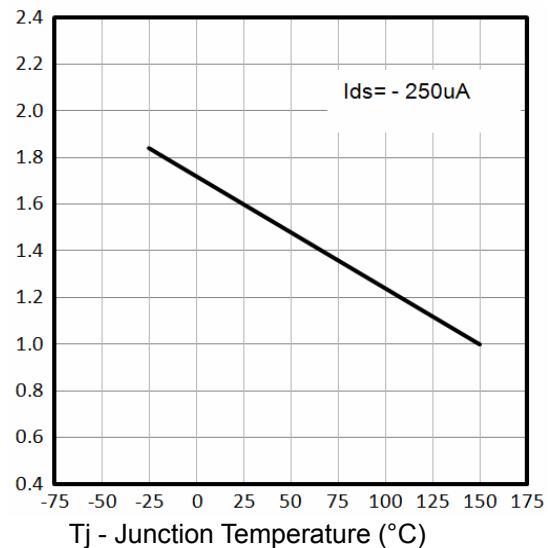


Fig2. Threshold Voltage Vs. Temperature

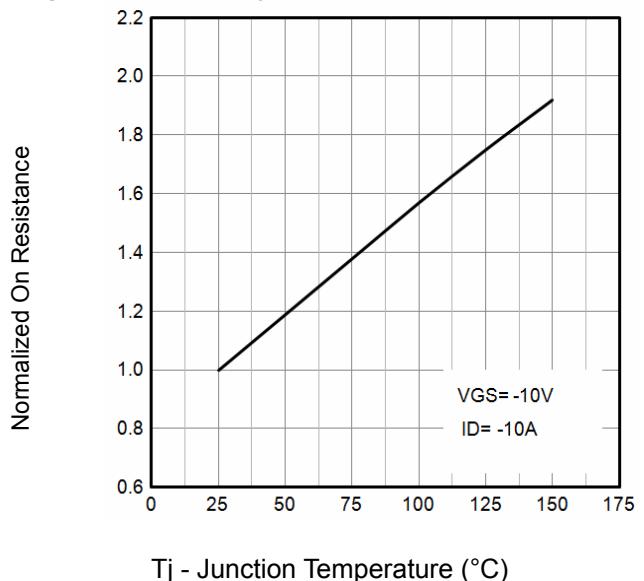


Fig4. Normalized On-Resistance Vs. Temperature

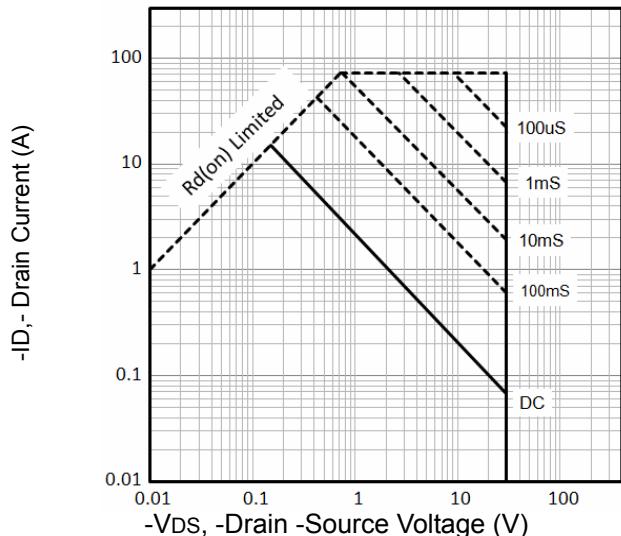


Fig6. Maximum Safe Operating Area

Typical Characteristics

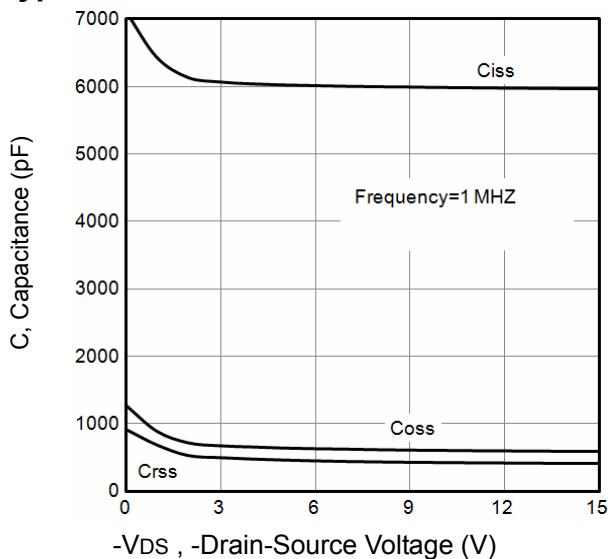


Fig7. Typical Capacitance Vs.Drain-Source Voltage

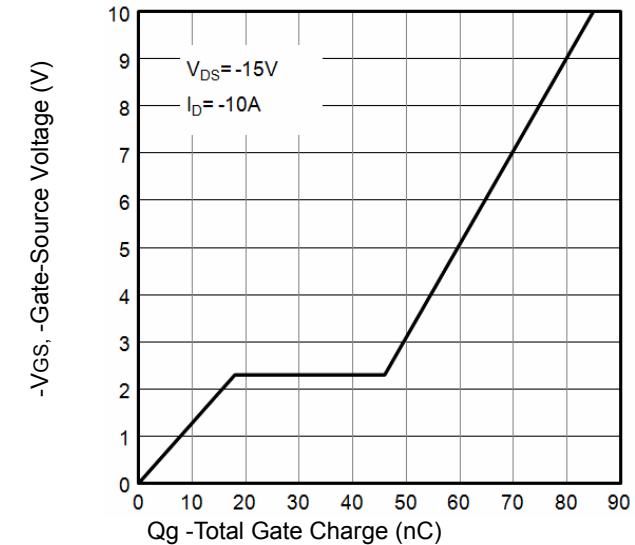


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

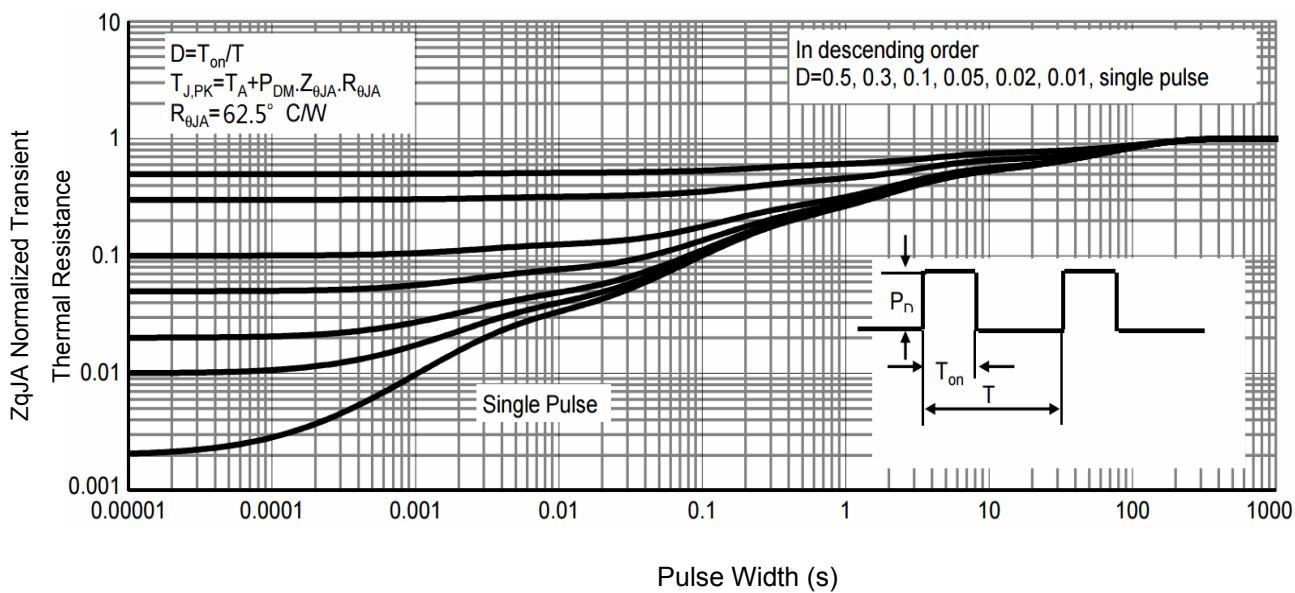


Fig9. Normalized Maximum Transient Thermal Impedance T_j -Junction

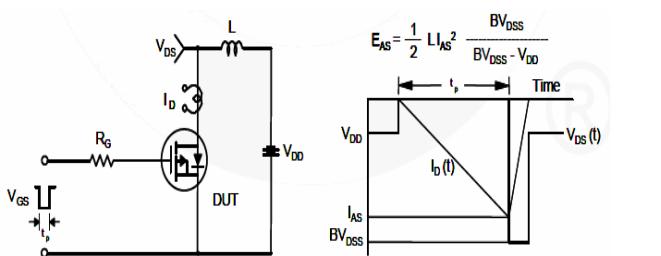


Fig10. Unclamped Inductive Test Circuit and Waveforms

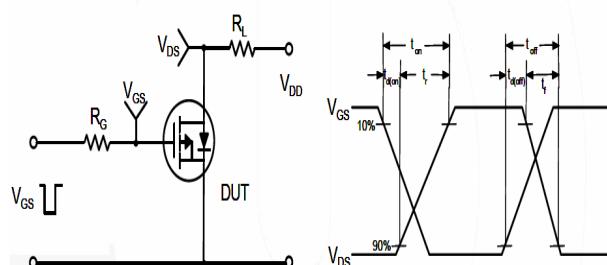
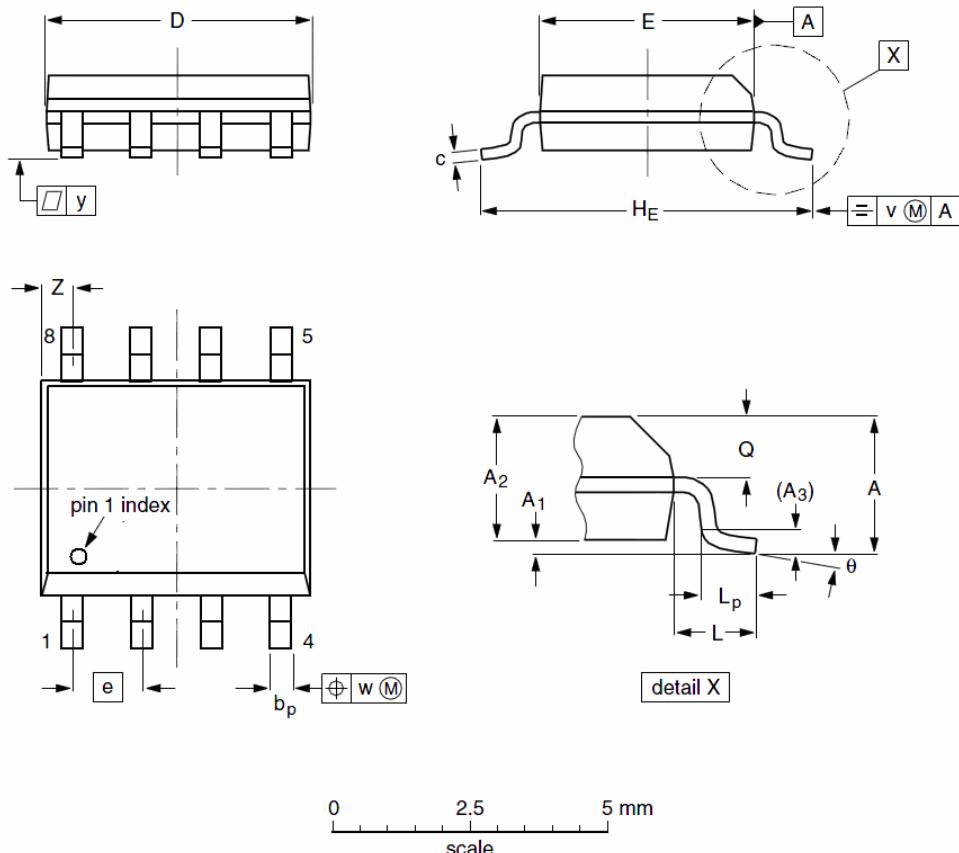


Fig11. Switching Time Test Circuit and waveforms

SOP8 Package Outline Data



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	--	1.75	--	A₁	0.10	0.18	0.25
A₂	1.25	1.35	1.45	A₃	--	0.25	--
b_p	0.36	0.42	0.49	c	0.19	0.22	0.25
D	4.80	4.92	5.00	E	3.80	3.90	4.00
e	--	1.27	--	H_E	5.80	5.98	6.20
L	--	1.05	--	L_p	0.40	0.68	1.00
Q	0.60	0.65	0.70	v	--	0.25	--
w	--	0.25	--	y	--	0.10	--
Z	0.30	0.50	0.70	θ	0°		8°

Customer Service

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